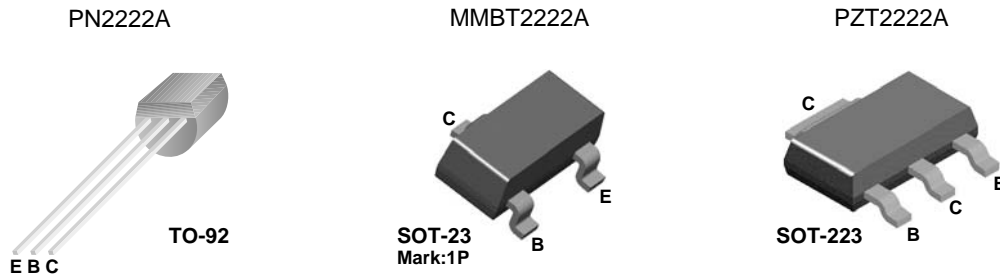


# PN2222A/MMBT2222A/PZT2222A

## NPN General Purpose Amplifier

- This device is for use as a medium power amplifier and switch requiring collector currents up to 500mA.
- Sourced from process 19.



### Absolute Maximum Ratings \* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{CBO}$	Collector-Base Voltage	75	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current	1.0	A
$T_{STG}$	Operating and Storage Junction Temperature Range	- 55 ~ 150	$^\circ\text{C}$

\* This ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These rating are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Max.			Units
		PN2222A	*MMBT2222A	**PZT2222A	
$P_D$	Total Device Dissipation Derate above $25^\circ\text{C}$	625	350	1,000	mW
		5.0	2.8	8.0	mW/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	$^\circ\text{C}/\text{W}$

\* Device mounted on FR-4 PCB  $1.6'' \times 1.6'' \times 0.06''$ .

\*\* Device mounted on FR-4 PCB  $36\text{mm} \times 18\text{mm} \times 1.5\text{mm}$ ; mounting pad for the collector lead min.  $6\text{cm}^2$ .

**Electrical Characteristics**  $T_a = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
<b>Off Characteristics</b>					
$BV_{(BR)CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = 10\text{mA}, I_B = 0$	40		V
$BV_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}, I_E = 0$	75		V
$BV_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}, I_C = 0$	6.0		V
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 60\text{V}, V_{EB(off)} = 3.0\text{V}$		10	nA
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = 60\text{V}, I_E = 0$ $V_{CB} = 60\text{V}, I_E = 0, T_a = 125^\circ\text{C}$		0.01 10	$\mu\text{A}$ $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = 3.0\text{V}, I_C = 0$		10	nA
$I_{BL}$	Base Cutoff Current	$V_{CE} = 60\text{V}, V_{EB(off)} = 3.0\text{V}$		20	nA
<b>On Characteristics</b>					
$h_{FE}$	DC Current Gain	$I_C = 0.1\text{mA}, V_{CE} = 10\text{V}$ $I_C = 1.0\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}$ $I_C = 10\text{mA}, V_{CE} = 10\text{V}, T_a = -55^\circ\text{C}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}^*$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}^*$	35 50 75 35 100 50 40	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage *	$I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$		0.3 1.0	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage *	$I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$	0.6	1.2 2.0	V V
<b>Small Signal Characteristics</b>					
$f_T$	Current Gain Bandwidth Product	$I_C = 20\text{mA}, V_{CE} = 20\text{V}, f = 100\text{MHz}$	300		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		8.0	pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5\text{V}, I_C = 0, f = 1\text{MHz}$		25	pF
$rb'C_c$	Collector Base Time Constant	$I_C = 20\text{mA}, V_{CB} = 20\text{V}, f = 31.8\text{MHz}$		150	pS
NF	Noise Figure	$I_C = 100\mu\text{A}, V_{CE} = 10\text{V},$ $R_S = 1.0\text{K}\Omega, f = 1.0\text{KHz}$		4.0	dB
$Re(h_{ie})$	Real Part of Common-Emitter High Frequency Input Impedance	$I_C = 20\text{mA}, V_{CE} = 20\text{V}, f = 300\text{MHz}$		60	$\Omega$
<b>Switching Characteristics</b>					
$t_d$	Delay Time	$V_{CC} = 30\text{V}, V_{EB(off)} = 0.5\text{V},$ $I_C = 150\text{mA}, I_{B1} = 15\text{mA}$		10	ns
$t_r$	Rise Time			25	ns
$t_s$	Storage Time	$V_{CC} = 30\text{V}, I_C = 150\text{mA},$ $I_{B1} = I_{B2} = 15\text{mA}$		225	ns
$t_f$	Fall Time			60	ns

\* Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

# Typical Characteristics

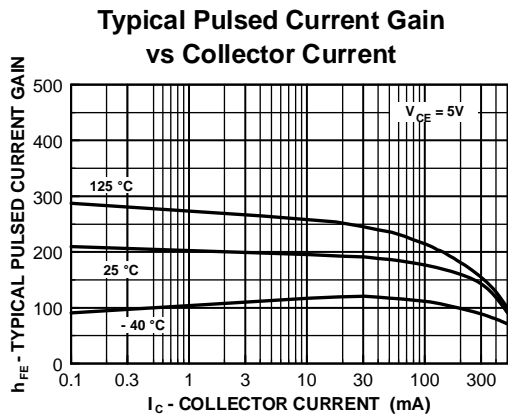


Figure 1. Typical Pulsed Current Gain vs Collector Current

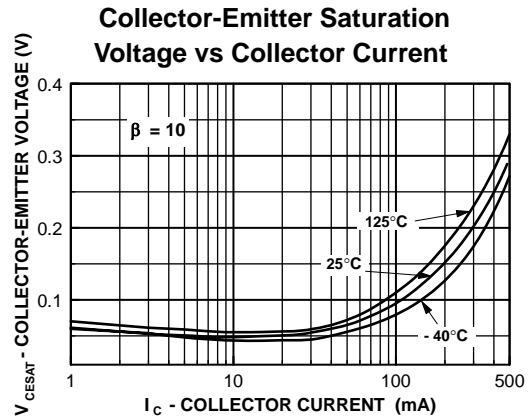


Figure 2. Collector-Emitter Saturation Voltage vs Collector Current

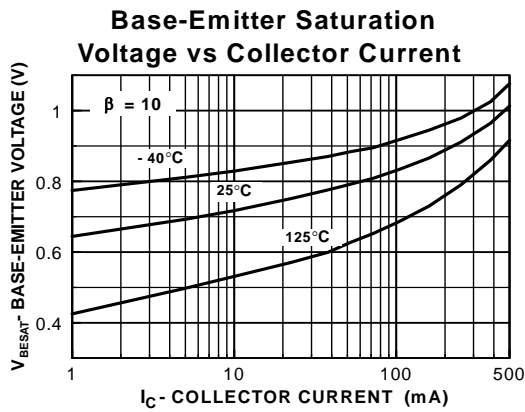


Figure 3. Base-Emitter Saturation Voltage vs Collector Current

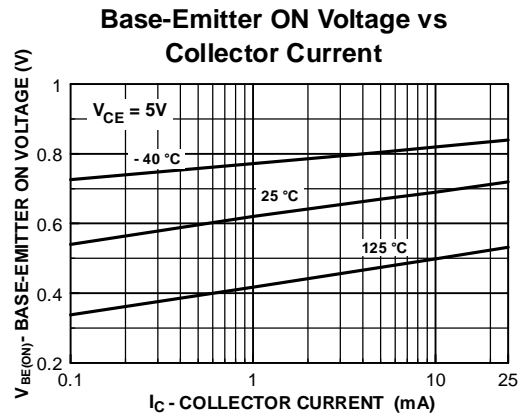


Figure 4. Base-Emitter On Voltage vs Collector Current

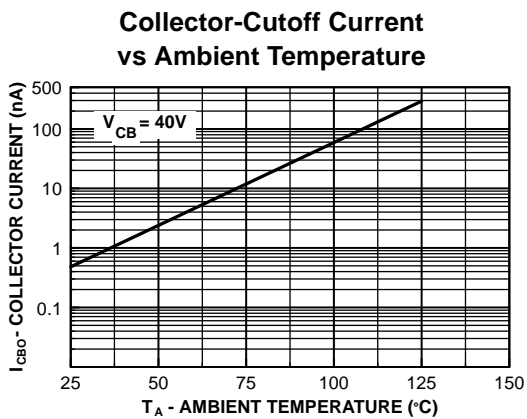


Figure 5. Collector Cutoff Current vs Ambient Temperature

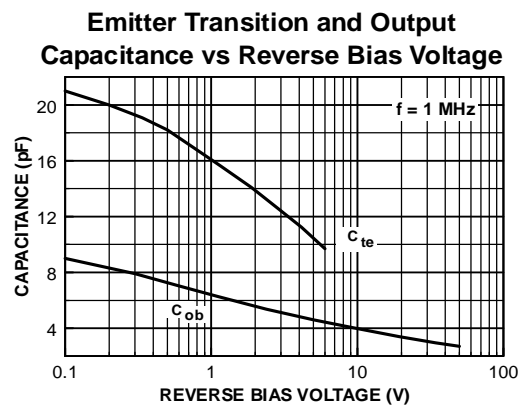


Figure 6. Emitter Transition and Output Capacitance vs Reverse Bias Voltage

# Typical Characteristics

**Turn On and Turn Off Times vs Collector Current**

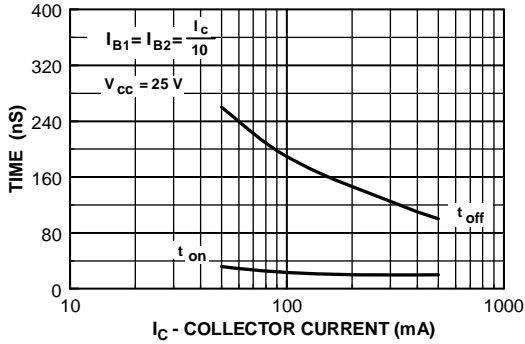


Figure 1. Turn On and Turn Off Times vs Collector Current

**Switching Times vs Collector Current**

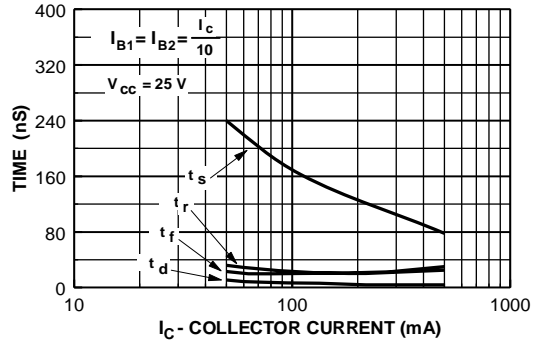


Figure 2. Switching Times vs Collector Current

**Power Dissipation vs Ambient Temperature**

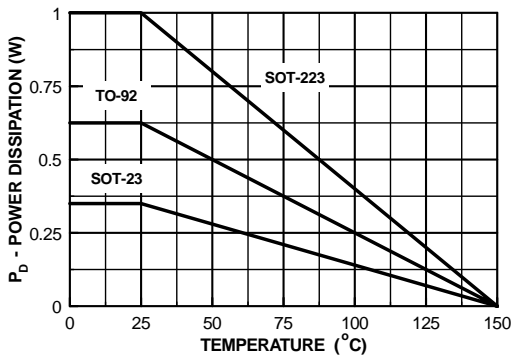


Figure 3. Power Dissipation vs Ambient Temperature

**Common Emitter Characteristics**

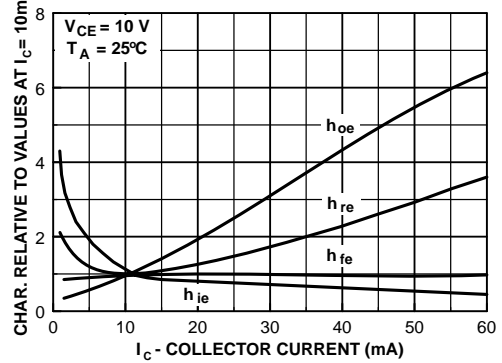


Figure 4. Common Emitter Characteristics

**Common Emitter Characteristics**

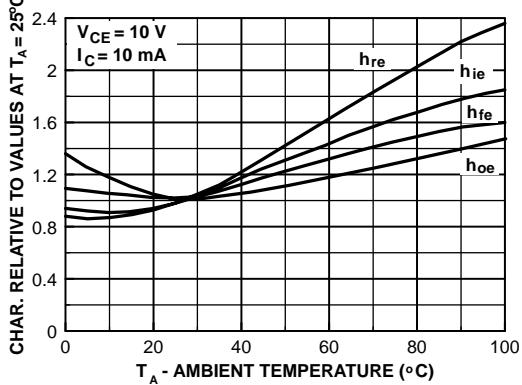


Figure 5. Common Emitter Characteristics

**Common Emitter Characteristics**

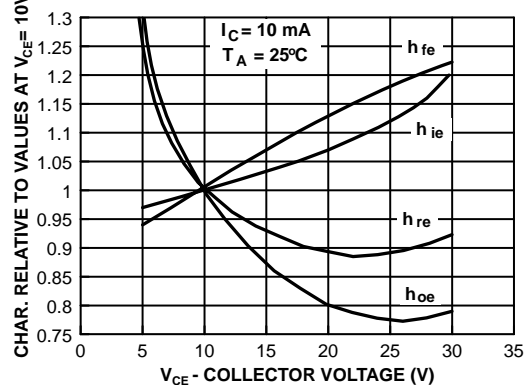





Figure 6. Common Emitter Characteristics



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